



1. Features

- The device is a PNP transistor manufactured by using planar Technology resulting in rugged highperformance devices.
- The complementary NPN type is 2SD882.

TO-126



2. Mechanical Data

- Case:Molded Plastic,TO-126 .
- Epoxy:UL 94V-0 rate flame retardant.
- Terminals:Plated Leads Solderable per MIL-STD-750,Method-2026.
- Marking:marked on body.

3. Maximum Ratings and Electrical Characteristics

Electrical Characteristics Rating at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BV_{CBO}	-40	V
Collector-Emitter Voltage	BV_{CEO}	-30	V
Emitter-Base Voltage	BV_{EBO}	-5	V
Collector Current	I_C	-3	A
Collector Power Dissipation	P_C	1.25	W
Power Dissipation	T_j	150	°C
Storage Temperature	T_{slg}	-55~150	°C

4.Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Value			UNIT
			Min	Typ	Max	
Collector-base breakdown voltage	BV_{CBO}	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-10	μA
DC current gain	h_{FE1}	$V_{CE}=-2\text{V}, I_B=-20\text{mA}$	50			
	h_{FE2}	$V_{CE}=-2\text{V}, I_B=-1\text{A}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-0.5	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-2	V
Transition frequency	fT	$V_{CE}=-5\text{V}, I_B=-0.1\text{A}$	50			MHz

5.hFE Classification and Marking

Classification	Q	P	E
Range	100-200	160-320	200-400
Marking	2SB772Q	2SB772P	2SB772E



6. Rating And Characteristic Curves

Fig. 1 Static Characteristic

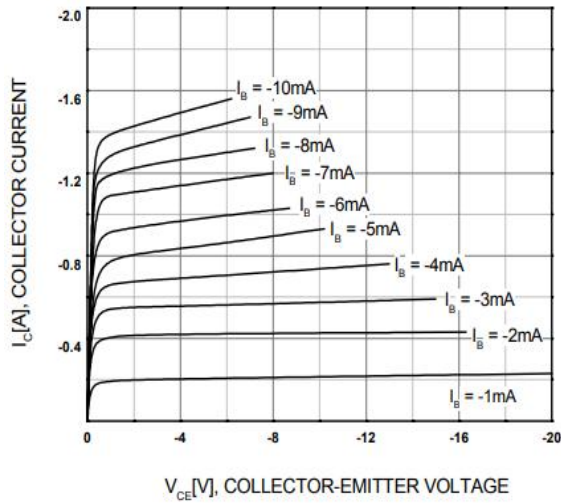


Fig. 2 DC current Gain

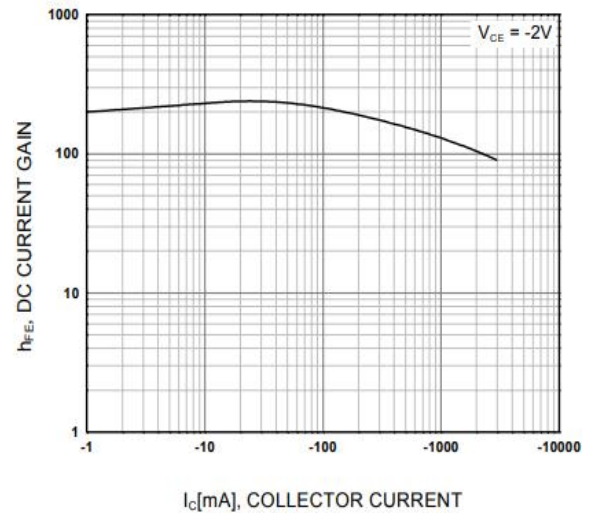


Fig. 3 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

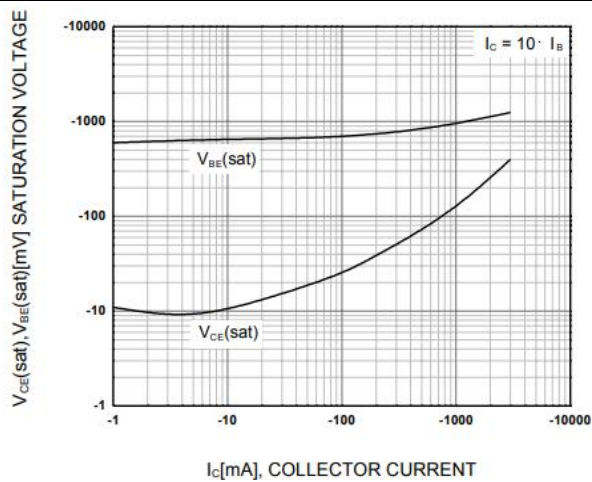


Fig.4 Collector Output Capacitance

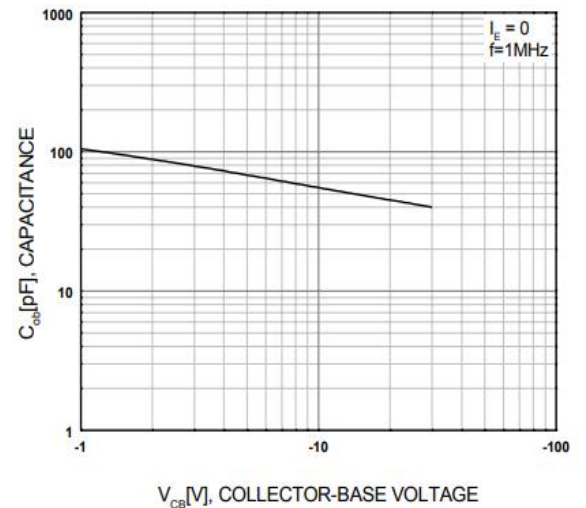


Fig.5 Current Gain Bandwidth Product

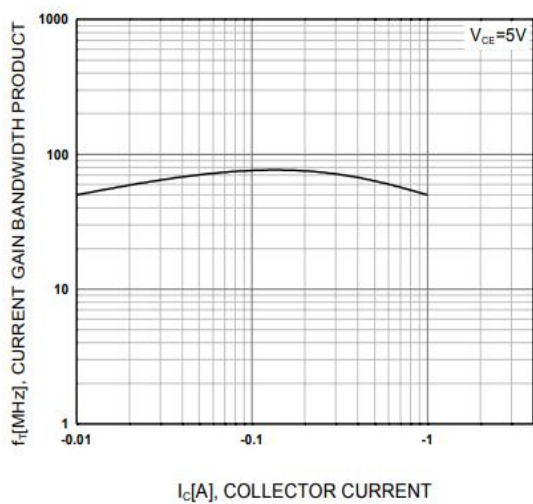
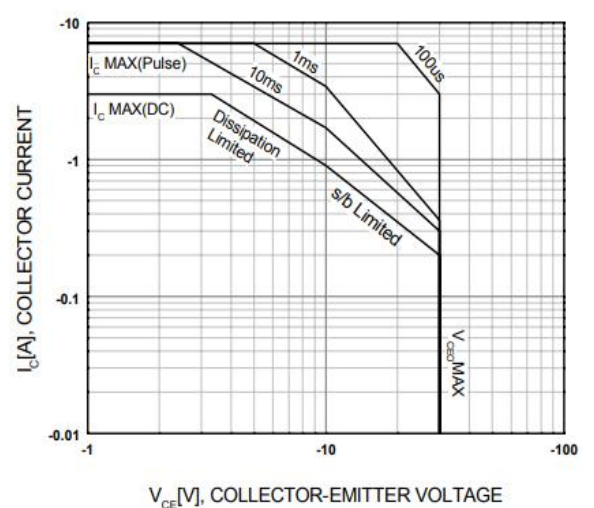
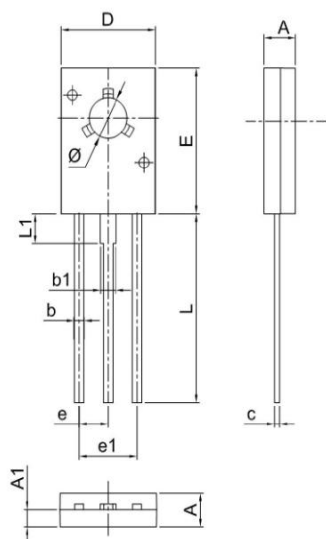


Fig.6 Power Derating



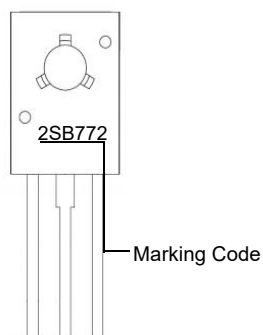


7. Dimensions



Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
A	0.094	0.114	2.40	2.90
A1	0.035	0.055	0.90	1.40
b	0.026	0.034	0.66	0.86
b1	0.046	0.054	1.17	1.37
c	0.015	0.024	0.38	0.60
D	0.287	0.315	7.30	8.00
E	0.417	0.433	10.60	11.00
e	0.089	0.092	2.25	2.33
e1	0.177	0.183	4.50	4.66
L	0.531	0.591	13.50	15.00

8. Part Marking System



9. Package Information

Package	Quantity(pcs)
2SB772	500



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